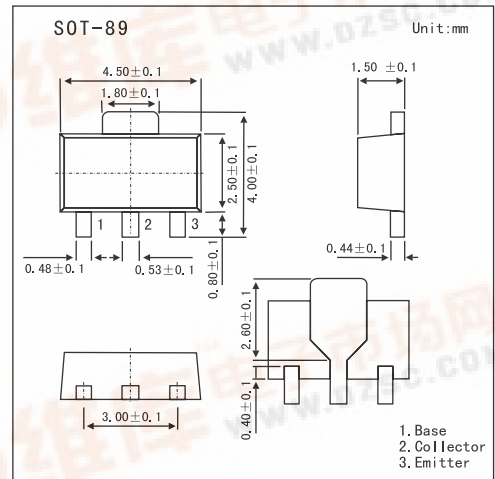


SMD Type Transistors

Power Transistor  
2SB1260

■ Features

- High breakdown voltage and high current.  $V_{CE0} = -80V, I_c = -1A$
- Good hFE linearity.
- Low  $V_{CE(sat)}$ .
- Epitaxial planar type
- PNP silicon transistor



■ Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-80	V
Collector-emitter voltage	$V_{CEO}$	-80	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_c$	-1	A
Collector current(Pulse)	$I_{CP}^*$	-2	A
Collector power dissipation	$P_c$	0.5	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\* Single pulse,  $P_w = 100ms$

■ Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$BV_{CBO}$	$I_c = -50\mu A$	-80			V
Collector-emitter breakdown voltage	$BV_{CEO}$	$I_c = -1mA$	-80			V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E = -50\mu A$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -60V$			-1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4V$			-1	$\mu A$
Collector-emitter saturation voltage	$h_{FE}$	$V_{CE} = -3V, I_c = -0.1A$	82		390	
DC current transfer ratio	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$			-0.4	V
Transition frequency	$C_{ob}$	$V_{CE} = -5V, I_E = 50mA, f = 30MHz$		100		MHz
Output capacitance	$f_t$	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		25		pF

■ hFE Classification

Marking	BE		
	P	Q	R
hFE	82~180	120~270	180~390

